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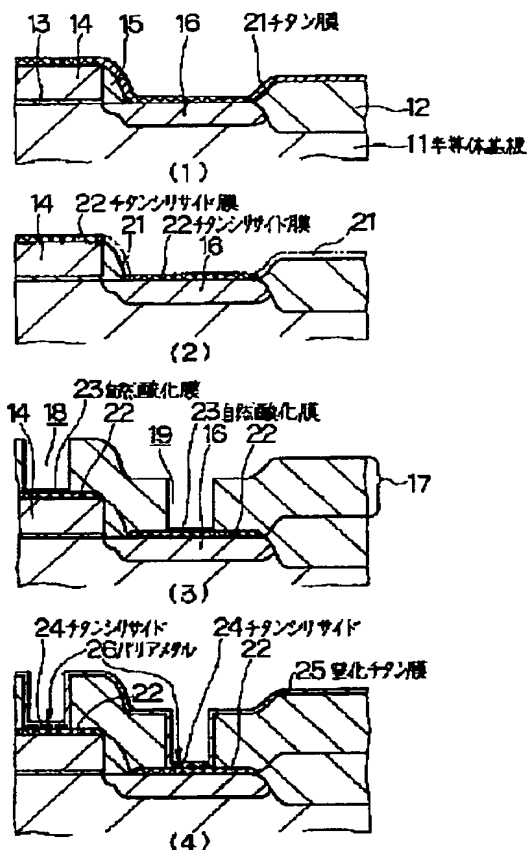
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TITLE : METHOD OF FORMING BARRIER
METAL



ABSTRACT ► **PURPOSE:** To enhance a barrier metal in ohmic contact property and step coverage by a method wherein a natural oxide film is removed from a silicide film by a hydrogen reducing reaction, and a barrier metal is formed through a CVD method without exposing the silicide film to an oxidizing atmosphere.

CONSTITUTION: A natural oxide film 23 formed on a titanium silicide film 22 is removed through a hydrogen reducing reaction, and a titanium nitride (TiN) film 25 is formed through a chemical vapor deposition method without exposing the silicide film 22 to an oxidizing atmosphere for the formation a barrier metal 26.

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